



SDI Review Form 1.6

Journal Name:	Physical Science International Journal
Manuscript Number:	Ms_PSIJ_29024
Title of the Manuscript:	Influence of Annealing Temperature on the Physical Properties of Polycrystalline Cu ₂ SnSe ₃ Thin Films Prepared by Thermal Vacuum Evaporation Technique
Type of the Article	Original Research Article

General guideline for Peer Review process:

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.

To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

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PART 1: Review Comments

	Reviewer's comment	Author's comment (if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)
<u>Compulsory</u> REVISION comments	Experimental Paragraph 1 line 2 delete the second point. Paragraph 1 line 4 the I-V characteristic of the films has been investigated by using the Van der Pauw method or by Keithley 2700 Multimeter/Data Acquisition System?? 3.1 Scanning Electron Microscopy (SEM) Paragraph 1 line 4 delete colon in mechanical properties and rewrite this line ... mechanical, properties, etc. of Cu₂SnSe₃ thin films with is surface morphology. Paragraph 1 line 4 to 6 Delete... Morphological investigations were carried out on six samples of Cu₂SnSe₃ thin films annealed at different temperatures using scanning electron microscope (SEM). Because the last paragraph corresponds to experimental procedure Paragraph 1 line 6 To change times by x. Paragraph 1 line 7 delete... in Figures 1 and 2, almost finish. Results 3.1 Paragraph 3 line 3 the authors must show the micro cracks to 400 and 500 C. Because in the images these seem needles and elongated particles as fibers. 3.2 Paragraph 1 line 6, review if the information corresponds to figure 3 or table No.1 Figure 5.26?.	



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	For figure 3 to include the results of the EDS in the spectrum (quantification as shows the system), because in the figure No.3, it not possible to observe as peaks decrease when the temperature increases. The thin films were obtained by Thermal Vacuum Evaporation Technique, however are low references about this technique, the authors compared their results with other techniques and they affirm that "well known that morphology of semiconductor thin films are influenced by the method of synthesis and the annealing temperature employed" According to the results in the table No.1 when the temperature increases the copper decreases, but, from being deposited, the material does not have the stoichiometric ratio. It is recommended to verify and include the composition of the starting material before evaporation Delete figure 4 and 5 are not necessities. After ec. 4, line 2, delete conductivity. Delete one, table No.2 or figure 7, they content the same information. Conclusions Delete deposition technique, because the authors did not have two process or more to compare. Cu₂SnSe₃ films show a strong dependence on the film deposition technique. The atomic stoichiometric ratio for Cu₂SnSe₃ is 33.33, 16.67 and 50 approx. respectively. And neither thin film has the same.	
<u>Minor</u> REVISION comments		
<u>Optional/General</u> comments		

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